

IN THE CLAIMS:

Please cancel claims 1-20 and add new claims 21-39 as follows:

1-20. (Cancelled)

21. (New) A method for depositing a film to a substrate within a process chamber by an atomic layer deposition technique, comprising:

- introducing a precursor to the process chamber;
- absorbing the precursor to the substrate;
- purging the process chamber with a purge gas;
- introducing a process gas comprising the precursor and a reactant;
- reacting the absorbed precursor with the process gas to deposit the film; and
- purging the process chamber with the purge gas.

22. (New) The method of claim 21, wherein the film comprises copper.

23. (New) The method of claim 22, wherein the precursor comprises a copper precursor.

24. (New) The method of claim 23, wherein the copper precursor is copperhexafluoracetylacetonate trimethylvinylsilane.

25. (New) The method of claim 23, wherein the reactant comprises water.

26. (New) The method of claim 25, wherein the purge gas is selected from the group consisting of argon, nitrogen, hydrogen and combinations thereof.
27. (New) A method for depositing a metal-containing film to a substrate within a process chamber by an atomic layer deposition technique, comprising:
- introducing a metal-containing precursor to the process chamber;
 - absorbing the metal-containing precursor to the substrate;
 - purging the process chamber with a purge gas;
 - introducing a process gas comprising the metal-containing precursor and a gaseous catalyst;
 - chemically reducing the absorbed metal-containing precursor with the process gas to deposit the metal-containing film; and
 - purging the process chamber with the purge gas.
28. (New) The method of claim 27, wherein the metal-containing film comprises copper.
29. (New) The method of claim 28, wherein the metal-containing precursor comprises a copper precursor.
30. (New) The method of claim 29, wherein the copper precursor is copperhexafluoracetylacetonate trimethylvinylsilane.
31. (New) The method of claim 29, wherein the gaseous catalyst comprises water.

32. (New) The method of claim 31, wherein the purge gas is selected from the group consisting of argon, nitrogen, hydrogen and combinations thereof.

33. (New) A method for depositing a copper-containing film to a substrate within a process chamber by an atomic layer deposition technique, comprising:

introducing a copper precursor to the process chamber;

absorbing the copper precursor to the substrate;

purging the process chamber with a purge gas;

introducing a process gas comprising the copper precursor and a reactant;

reacting the absorbed copper precursor with the process gas; and

purging the process chamber with the purge gas.

34. (New) The method of claim 33, wherein the copper precursor is copperhexafluoracetylacetonate trimethylvinylsilane.

35. (New) The method of claim 33, wherein the reactant comprises water.

36. (New) The method of claim 34, wherein the reactant comprises water.

37. (New) The method of claim 35, wherein the purge gas is selected from the group consisting of argon, nitrogen, hydrogen and combinations thereof.

38. (New) A method of growing a thin film onto a substrate located within a reaction chamber comprising feeding a precursor of the film into the reaction chamber, causing the precursor to adsorb onto the surface of the substrate to form a layer thereof, and feeding a catalyst and the precursor into the reaction chamber in amounts to

substantially convert the layer of the precursor to the thin film, wherein the precursor comprises copperhexafluoracetylacetonate trimethylvinylsilane.

39. (New) The method of claim 38, wherein the catalyst comprises water and the film comprises copper.